INCH-POUND
MIL-M-38510/110C
19 August 2003
SUPERSEDING
MIL-M-38510/110B
11 September 1989

MILITARY SPECIFICATION

MICROCIRCUITS, LINEAR, QUAD OPERATIONAL AMPLIFIERS, MONOLITHIC SILICON

Reactivated after 20 August 2003 and may be used for either new or existing design acquisitions.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product herein shall consist of this specification sheet and MIL-PRF-38535.

1. SCOPE

- 1.1 <u>Scope</u>. This specification covers the detail requirements for monolithic silicon, quad operational amplifiers. Two product assurance classes and a choice of case outlines and lead finish are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).
 - 1.2 Part number. The complete part number should be in accordance with MIL-PRF-38535.
 - 1.2.1 <u>Device types</u>. The device types are internally compensated and should be as shown as follows:

Device type	<u>Circuit</u>
01 <u>1</u> /	Quad operational amplifier, medium power
02 <u>2</u> /	Quad operational amplifier, medium power,
	under compensated version of device type 01
03	Quad operational amplifier, medium speed, low noise
04	Quad operational amplifier medium speed, low noise (alternate pin out)
05 <u>3</u> /	Quad operational amplifier, single supply, low power
06 <u>3</u> /	Quad operational amplifier, single supply, low power

1.2.2 Device class. The device class should be the product assurance level as defined in MIL-PRF-38535.

Comments, suggestions, or questions on this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, 3990 East Broad St., Columbus, OH 43216-5000, or emailed to linear@dscc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at www.dodssp.daps.mil.

AMSC N/A FSC 5962

<u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

^{1/} Devices may be monolithic or they consist of two separate independent die.

^{2/} Device type 02 wideband amplifier is under compensated and can only be used with a closed loop gain of five or greater.

^{3/} Device types 05 and 06, single supply amplifiers, can be used with dual supplies, however, because of its class B output stage, the crossover distortion in the output signal may be unacceptable for the application.

1.2.3 Case outlines. The case outlines should be designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
A <u>4</u> /	GDFP5-F14 or CDFP6-F14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
Z	GDFP1-G14	14	Flat pack with gullwing leads

1.3 Absolute maximum ratings.

 _	
Supply voltage range :	
Device types 01, 02, 03, and 04	±22 V dc <u>5</u> /
Device types 05 and 06	
Input voltage range:	
Device types 01, 02, 03, and 04	±20 V dc 6/
Device types 05 and 06	$-V_{CC} - 0.3 \text{ V to } +V_{CC}$
Differential input voltage range	
Input current range:	_
Device types 01 and 02	
Device types 03, 04, 05, and 06	
Storage temperature range	
Output short-circuit duration	
Lead temperature (soldering, 60 seconds)	
Junction temperature (T _J)	+175°C <u>9</u> /
Thermal resistance, junction-to-case (θ_{JC}):	
Cases A, C, D, and Z	See MIL-STD-1835
1.4 Recommended operating conditions.	
Supply voltage range:	
Device types 01, 02, 03, and 04	±5 V dc to ±20 V dc
Device types 05 and 06	±5 V dc to +30 V dc
Ambient temperature range (T _A)	-55°C to +125°C

^{4/} Inactive package case outline.

^{5/} Voltages in excess of these may be applied for short-term tests if voltage difference does not exceed 44 volts (36 volts for device types 05 and 06).

^{6/} For device types 01 through 04, for supply voltages less than ±20 V dc, the absolute maximum input voltage is equal to the supply voltage. For device types 05 and 06, for supply voltages differences of less than 36 V, the absolute maximum input voltage is equal to the supply voltage.

^{7/} The differential input voltage range should not exceed the supply voltage range.

^{8/} Short circuit may be to ground or either supply. Rating applies to +125°C case temperature or +75°C ambient temperature.

 $[\]underline{9}$ / For short term test (in the specific burn-in and life test configuration when required and up to 168 hours maximum) T_J = +275°C.

1.5 Power and thermal characteristics.

Case outlines	Maximum allowable power	Maximum	Maximum
	dissipation	θJC	hetaJA
A, D	350 mW at T _A = +125°C	60°C/W	140°C/W
С	400 mW at T _A = +125°C	35°C/W	120°C/W
Z	350 mW at T _A = +125°C	25°C/W	176°C/W still air
			116°C/W 500 LFPM

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications, standards, and handbooks</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard for Microelectronics.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this document and the references cited herein the text of this document shall takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 Qualification. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).
- 3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.3 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.
 - 3.3.1 Terminal connections. The terminal connections shall be as specified on figure 1.
- 3.3.2 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request upon request.
 - 3.3.3 Case outlines. The case outlines shall be as specified in 1.2.3.
 - 3.3.4 Packaging and sealing material. Package and sealing material shall be in accordance with MIL-PRF-38535.
 - 3.4 Lead material and finish. Lead material and finish shall be in accordance with MIL-PRF-38535.
- 3.5 <u>Electrical performance characteristics</u>. The following electrical performance characteristics are as specified in table I, and apply over the full ambient operating temperature range of -55°C to +125°C and for supply voltages as follows. Unless otherwise specified, source resistance (Rs) shall be 50 Ω for all tests.

Device types 01, 02, 03, and 04 will have a dual power supply with $\pm V_{CC}$ (min) at ± 5 V and $\pm V_{CC}$ (max) at ± 20 V. Device types 05 and 06 will have a single power supply with $\pm V_{CC}$ (min) at ± 5 V and $\pm V_{CC}$ (max) at ± 30 V.

- 3.5.1 <u>Instability oscillations</u>. The devices shall be free of oscillations when operated in the test circuits of this specifications.
- 3.6 <u>Electrical test requirements</u>. Electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.
 - 3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.
- 3.8 <u>Microcircuit group assignment</u>. The devices covered by this specification shall be in microcircuit group number 49 (see MIL-PRF-38535, appendix A).

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lir	mits	Unit	
		unless otherwise specified			Min	Max		
Input offset voltage	V _{IO}	1/	1	01,02, 04,05		±5	mV	
				03		±3		
				06		±2	1	
			2,3	01,02, 04		±6	1	
				03		±5		
						05		±7
				06		±4		
Input offset voltage temperature sensitivity	ΔV _{IO} / ΔT		2	01,02, 04		±25	μV/°C	
				03		±20		
				05,06		±30		
		3	01,02, 04		±25			
				03		±20		
				05,06		±30		

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions -55°C ≤ T _A ≤ +125°C see figure 2	Group A subgroups	Device type		mits	Unit
		unless otherwise specified			Min	Max	
Input offset current	lio	$R_S = 50 \Omega$ 1/	1,2	01,02		±25	nA
				03,05		±30	
				04		±75	
				06		±10	
			3	01,02, 03,05		±75	
				04		±150	
				06		±30	
Input offset current temperature sensitivity	ΔI _{IO} / ΔΤ		2	01,02, 03		±200	pA/°C
				04		±500	
				05,06		±400	
			3	01,02		±400	
				03		±500	
				04		±1000	
				05,06		±700	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Input bias current	+l _{IB}	$+I_{IB}$ $R_S = 20 \text{ k}\Omega$ 1/	1,2	01,02	-0.1	100	nA
				03	-200	+0.1	
				04	-250	+0.1	
				05	-150	+0.1	
				06	-50	+0.1	-
			3	01,02	-0.1	325	-
				03	-325	+0.1	-
				04	-400	+0.1	
				05	-300	+0.1	-
				06	-100	+0.1	
	-I _{IB}		1,2	01,02	-0.1	100	-
				03	-200	+0.1	
				04	-250	+0.1	
				05	-150	+0.1	
				06	-50	+0.1	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $-55^{\circ}C \le T_A \le +125^{\circ}C$ see figure 2	Group A subgroups	Device type	Lir	mits	Unit
		unless otherwise specified			Min	Max	
Input bias current	-I _{IB}	$R_S = 20 \text{ k}\Omega \underline{1}/$	3	01,02	-0.1	325	nA
				03	-325	+0.1	
				04	-400	+0.1	
				05	-300	+0.1	
				06	-100	+0.1	
Power supply rejection ratio	+PSRR	+V _{CC} = 10 V, -V _{CC} = -20 V	1,2,3	01,02, 03,04		±100	μV/V
14.10		+V _{CC} = 30 V to 5 V		05,06		±100	
	-PSRR	+V _{CC} = 20 V, -V _{CC} = -10 V		01,02, 03,04		±100	
Input voltage common mode rejection	CMR	V _{CM} = 30 V <u>2</u> /	1,2,3	01,02, 03,04	76		dB
		V _{CM} = 28 V <u>2</u> /		05,06	76		
Output short-circuit current (for positive	IOS(+)	$\pm V_{CC} = \pm 15 \text{ V}, \qquad \underline{3}/$	1,2	01,02	-55		mA
output)		t ≤ 25 ms, only one amplifier shorted to GND at one time		03,04	-80		
		\pm V _{CC} = 30 V, $\underline{3}$ / t \leq 25 ms, only one amplifier shorted to GND at one time		05,06	-70		
		$\pm V_{CC} = \pm 15 \text{ V}, \qquad \underline{3}/$	3 <u>4</u> /	01,02	-75		
		t ≤ 25 ms, only one amplifier shorted to GND at one time		03,04	-80		
		$\pm V_{CC}$ = 30 V, $\underline{3}/$ t \leq 25 ms, only one amplifier shorted to GND at one time		05,06	-70		

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lim	nits	Unit
		unless otherwise specified			Min	Max	
Output short-circuit current (for negative output	IOS(-)	$\pm V_{CC} = \pm 15 \text{ V},$ $3/$ t $\leq 25 \text{ ms}, \text{ only one}$ amplifier shorted to GND at one time	1,2	01,02		55	mA
			3 <u>4</u> /	01,02		75	
				03,04		80	
Supply current	Icc	±V _{CC} = ±15 V <u>5</u> /	1,2	01,02		+3.6	mA
				03		+7	
				04		+11	
		+V _{CC} = 30 V <u>5</u> /		05,06		+3	
		±V _{CC} = ±15 V <u>5</u> /	3	01,02		+4.5	
				03		9	
				04		+13	
		V _{CC} = 30 V <u>5</u> /		05,06		+4	
Output voltage swing (maximum)	+V _{OP}	\pm V _{CC} = \pm 20 V, R _L = 10 kΩ	4,5,6	01,02, 03,04	+16		V
,		$V_{CC} = 30 \text{ V}, R_L = 10 \text{ k}\Omega$		05,06	+27		
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{L} = 2 \text{ k}\Omega$		01,02, 03,04	+15		-
		$V_{CC} = 30 \text{ V}, R_L = 2 \text{ k}\Omega$		05,06	+26		
	-V _{OP}	\pm V _{CC} = \pm 20 V, R _L = 10 kΩ		01,02, 03,04		-16	
		$\pm V_{CC} = \pm 20 \text{ V}, \text{ R}_{L} = 2 \text{ k}\Omega$		01,02, 03,04		-15	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test		Symbol	Conditions $-55^{\circ}C \le T_{A} \le +125^{\circ}C$ see figure 2	Group A subgroups	Device type	Lir	mits	Unit			
			unless otherwise specified			Min	Max				
Single ended open	<u>6</u> /	A _{VS} (+)	$\pm V_O = \pm 15 \text{ V},$	4	01,02, 03,04	50		V/mV			
loop voltage gain			$R_L = 10 \text{ k}\Omega$								
			$V_0 = 1 \text{ V to } 26 \text{ V},$		05,06	50					
			R _L = 10 kΩ								
			$\pm V_0 = \pm 15 \text{ V},$	5,6	01,02, 03,04	25					
			R _L = 10 kΩ		03,04						
			$V_0 = 1 \text{ V to } 26 \text{ V},$		05,06	25					
			$R_L = 10 \text{ k}\Omega$								
		Avs(-)	$\pm V_{O} = \pm 15 \text{ V},$	4	01,02, 03,04	50					
			$R_L = 2 k\Omega$		03,04						
			$V_0 = 5 \text{ V to } 20 \text{ V},$		05,06	50					
			$R_L = 2 k\Omega$								
			$\pm V_{O} = \pm 15 \text{ V},$	5,6	01,02, 03,04	25					
			$R_L = 2 k\Omega$		03,04						
			$V_0 = 5 \text{ V to } 20 \text{ V},$		05,06	25					
			$R_L = 2 k\Omega$								
		Avs	$\pm V_{CC} = \pm 5 \text{ V}, V_O = \pm 2 \text{ V},$	4	01,02,	10					
			R_L = 10 kΩ and 2 kΩ		03,04						
			V _{CC} = 5 V,		05,06	10					
			$V_0 = 1 \text{ V to } 2.5 \text{ V},$								
			$R_L = 10 \text{ k}\Omega$ and $2 \text{ k}\Omega$								
			$\pm V_{CC} = \pm 5 \text{ V}, V_{O} = \pm 2 \text{ V},$	5,6	01,02,	10					
			$R_L = 10 \text{ k}\Omega$ and $2 \text{ k}\Omega$		03,04						
			V _C C = 5 V,		05,06	10					
			$V_0 = 1 \text{ V to } 2.5 \text{ V},$								
						$R_L = 10 \text{ k}\Omega$ and $2 \text{ k}\Omega$					

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Low level output voltage	V _{OL}	$+V_{CC} = 30 \text{ V}, \text{ R}_{L} = 10 \text{ k}\Omega$	4,5,6	05,06		35	mV
		+V _{CC} = 30 V, I _{OL} = 5 mA				1.5	V
		+V _{CC} = 4.5 V, I _{OL} = 2 μA				0.4	
High level output voltage	VoH	+V _{CC} = 30 V, I _{OH} = 10 mA	4,5,6	05,06	27		V
		+V _{CC} = 4.5 V, I _{OH} = 10 mA	4,5		2.4		
			6		2.3		
Transient response rise time	TR _(tr)	$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 1 \underline{7}/\text{see figure 4}$	7,8A,8B	01,02		1.0	μs
				03		0.2	
				04		0.3	
		\pm V _{CC} = \pm 20 V, A _V = 5 $\underline{7}$ / see figure 4		01,02		1.0	
		+V _{CC} = 30 V, A _V = 1 <u>7/</u> see figure 4		05,06		1.0	
Transient response overshoot	TR _(OS)	$\pm V_{CC} = \pm 20 \text{ V}, \underline{7}/$ see figure 4	7,8A,8B	01,02		25	%
				03		35	
				04		50	
		+V _{CC} = 30 V, <u>7/</u> see figure 4		05,06		60	

TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lir	nits	Unit
		unless otherwise specified			Min	Max	
Slew rate 9/	SR(+) and	$\pm V_{CC} = \pm 20 \text{ V}, \text{ A}_{V} = 1,$ see figure 5	7,8A,8B	01	+0.2		V/µs
	SR(-)			03	0.8		
				04	0.6		-
		\pm V _{CC} = \pm 20 V, A _V = 5, see figure 5		02	0.8		
		V _{CC} = 30 V, A _V = 1, see figure 5		05,06	0.1		
Noise (broadband)	NI(BB)	\pm V _{CC} = \pm 20 V, R _S = 50 Ω,	9	01,02		15	μV rms
		T _A = +25°C		03,04		5	
		\pm V _{CC} = ±15 V, R _S = 50 Ω, T _A = +25°C		05,06		15	
Noise (popcorn)	NI(PC)	$\pm V_{CC} = \pm 20 \text{ V}, \text{ Rs} = 20 \text{ k}\Omega,$	9	01,02		40	μV peak
		T _A = +25°C		03,04		50	
		$\pm V_{CC} = \pm 15 \text{ V}, R_S = 20 \text{ k}\Omega,$		05,06		50	
		T _A = +25°C					

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ see figure 2	Group A subgroups	Device type	Lir	mits	Unit
		unless otherwise specified			Min	Max	
Channel separation	CS	T _A = +25°C, see figure 7	7	01,02, 03,04, 05,06, 07,08	80		dB

- 1/ Device types 01 to 04 shall be tested at $V_{CM} = 0 \text{ V}$, +15 V, and -15 V with $\pm V_{CC} = \pm 20 \text{ V}$; and at $V_{CM} = 0 \text{ V}$ with $\pm V_{CC} = \pm 5 \text{ V}$. Device types 05 and 06 should be tested at $V_{CM} = -13 \text{ V}$ with $V_{CC} = 2 \text{ V}$ and $-V_{CC} = -28 \text{ V}$; $V_{CM} = +15 \text{ V}$ with $+V_{CC} = 30 \text{ V}$ and $-V_{CC} = 0 \text{ V}$; $V_{CM} = +1.4 \text{ V}$ with $V_{CC} = 5 \text{ V}$ and $-V_{CC} = 0 \text{ V}$; $V_{CM} = -1.1 \text{ V}$ at $\pm V_{CC} = 2.5 \text{ V}$.
- 2/ CMR is determined by measuring input offset voltage as follows:

Offset voltage			Device	e types			Units
condition		01 - 04		(05 and 06	3	
	+Vcc	-Vcc	Vo	+Vcc	-Vcc	Vo	
1	35	-5	15	30	0	15	V
2	5	-35	-15	2	-28	-13	V

- <u>3</u>/ Continuous limits will be considerably lower and apply for −55°C ≤ T_A ≤ 25°C.
- $\underline{4}/I_{SO(+)}$ and $I_{SO(-)}$ limits for device type 01 only at $T_A = -55$ °C are -75 mA and 75 mA respectively.
- 5/ ICC limits are the total for all four amplifiers at no load, connected as grounded followers.
- 6/ AVS(+) for device types 05 and 06 only.
- <u>7</u>/ Device types 05 and 06 transient response is specified with the input pulse referenced to 5 V. For application purposes the device may be operated with the input referenced to ground, however, saturation effects will cause the response time to increase by approximately 50 percent.

TABLE II. Electrical test requirements.

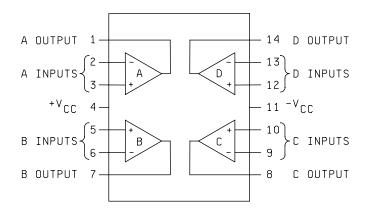
MIL-PRF-38535 test requirements	Subgroups ((see table III)
	Class S devices	Class B devices
Interim electrical parameters	1	1
Final electrical test parameters 1/	1,2,3,4	1,2,3,4
Group A test requirements	1,2,3,4,5,6, 7,8	1,2,3,4,5,6, 7,8
Group B electrical test parameters when using the method 5005 QCI option	1,2,3,4,5,6, 7,8	N/A
Group C end point electrical parameters	1,2,3, and table IV delta limits	1 and table IV delta limits
Group D end point electrical parameters	1,2,3	1

1/ PDA applies to subgroup 1.

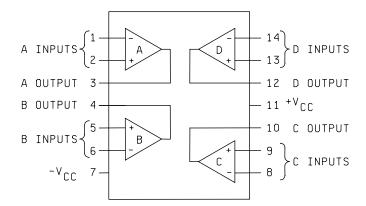
4. VERIFICATION.

- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as function as described herein.
- 4.2 <u>Screening</u>. Screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:
 - a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
 - c. Additional screening for space level product shall be as specified in MIL-PRF-38535.
 - 4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.

DEVICE TYPES 01,02,03,05 AND 06 CASES A,C,D AND Z SEE NOTE 1



DEVICE TYPE 04 CASES A AND C SEE NOTE 2



NOTES:

- 1. 14 lead flat pack, dual in line package, and gullwing flat pack.
- 2. 14 lead flat pack and dual in line package.

FIGURE 1. Case outlines and terminal connections.

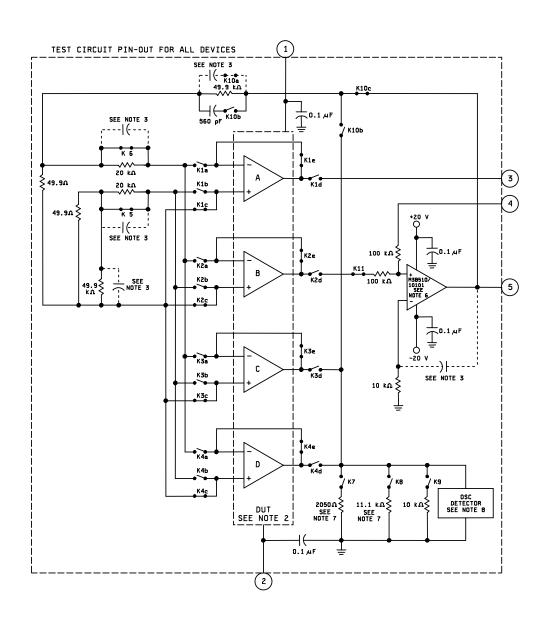


FIGURE 2. Test circuit for static tests.

NOTES:

- 1/ All resistors ± 0.1 percent tolerance and all capacitors are ± 10 % tolerance.
- 2/ Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state of relays (i.e. disable voltage supplies, current limit ±V_{CC}, etc.).
- 3/ Stabilizing capacitors may be added as required, if needed to prevent oscillations. Also, proper wiring procedures shall be followed to prevent oscillations. Loop response and settling time shall be consistent with the test rate such that any value has settled for at least five loop time constants before the value is measured, however, adequate settling time shall be allowed such that each parameter has settled to within five percent of its final value. There are two general methods to stabilize the test circuit: One method is with a capacitor in the nulling amplifier feedback loop and the other method is with a capacitor in parallel with the 49.9 kΩ closed loop feedback resistor. Both methods shall not be used simultaneously.
- 4/ All relays are shown in the normal de-energized state. Relays K1, K2, K3, and K4 select amplifiers A, B, C, and D respectively. The rest of the relays are used to select the conditions for each test.
- 5/ Each amplifier shall be tested separately, except for the ICC measurements where all the amplifiers shall be connected as grounded followers (relays K1 through K4 de-energized).
- 6/ The nulling amplifier should be an M38510/11001XXXor similar. Saturation of the nulling amplifier is not allowed on test where the E (pin 5) value is measured.
- 7/ The load resistors 2,050 Ω and 11.1 k Ω yield effective load resistances of 2 k Ω and 10 k Ω , respectively.
- 8/ Any oscillation greater that 300 mV in amplitude (peak peak) shall be a cause for device failure.

FIGURE 2. Test circuit for static tests- Continued.

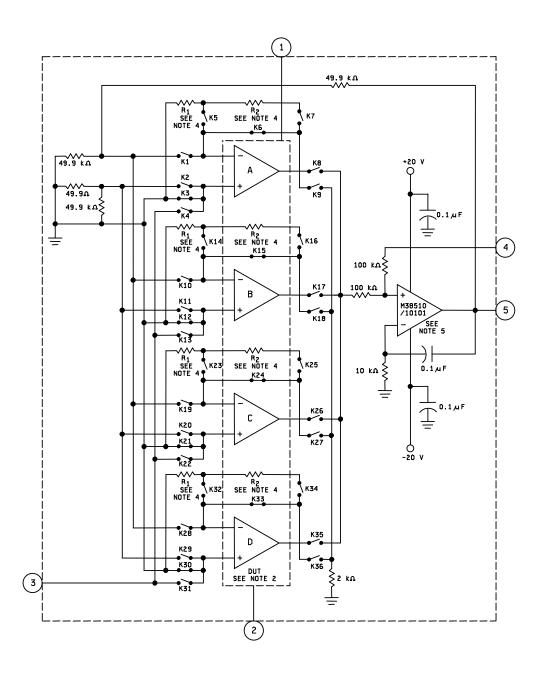


FIGURE 3. Test circuit for channel separation.

Test requirements.

CS test	Channels tested		Relays ene	ergized
		All c	levice types	Additional for device type 02
		Driven	Monitored	Driven
103 (100)	A to B	3,4,9	10,11,12,15,17	5,6,7
104 (101)	A to C	66	19,20,21,24,26	и
105 (102)	A to D	"	28,29,30,33.35	и
106 (103)	B to A	12,13,18	1,2,3,6,8	14,15,16
107 (104)	B to C	66	19,20,21,24,26	и
108 (105)	B to D	"	28,29,30,33,35	и
109 (106)	C to A	21,22,27	1,2,3,6,8	23,24,25
110 (107)	C to B	66	10,11,12,15,17	и
111 (108)	C to D	66	28,29,30,33,35	и
112 (109)	D to A	30,31,36	1,2,3,6,8	32,33,34
113 (110)	D to B	66	10,11,12,15,17	и
114 (111)	D to C	ű	19,20,21,24,26	и

^{*} Numbers in parenthesis apply to device types 05 and 06.

- 1/ All resistors are ± 0.1 % tolerance and all capacitors are ± 10 %.
- $\underline{2}$ / Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state relays (i.e. disable voltage supplies, current limit $\pm V_{CC}$, etc.).
- 3/ All relays are shown in the normal de-energized state. The above table shall be used to determine which relays to energize for each test.
- $\frac{4}{2}$ R₁ and R₂ shall be used with device type 02 only and shall be such that A_V = 5 V/V.
- 5/ The nulling amplifier shall be a M38510/11001XXX or similar. Saturation of the nulling amplifier is not allowed.

FIGURE 3. Test circuit for channel separation - Continued.

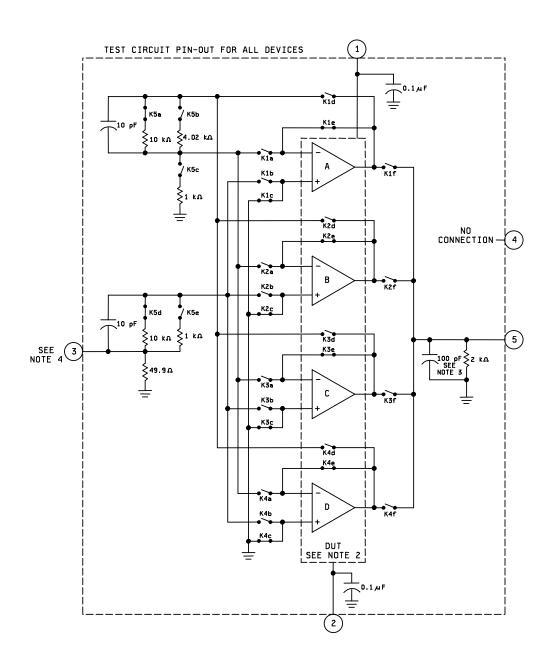
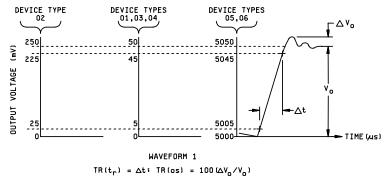
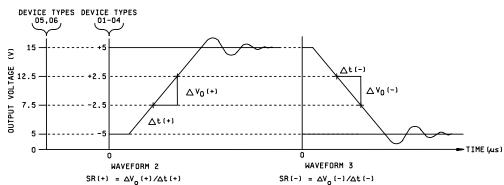


FIGURE 4. <u>Test circuit and waveform for transient response</u> .







- All resistors are ± 0.1 % tolerance and all capacitors are ± 10 % tolerance.
- Precautions shall be taken to prevent damage to the device under test during insertion into socket and change of state of relays (i.e. disable voltage supplies, current limit ±V_{CC}, etc.).
- This capacitance includes the actual measured value with stray and wire capacitance.
- Relays K1, K2, K3, and K4 select amplifiers A, B, C, and D respectively. Relay K5 shall be energized for device type 02 only. The input pulse shall have the following characteristics:

FIGURE 4. Test circuit and waveform for transient response - Continued.

Input pulse table

Parameter symbol	Device type	Rise time	Amplitude
TR(t _r)	01,03,04	50 ns or less	+50 mV referenced to GND
	02		+250 mV referenced to GND
	05,06		+50 mV referenced to 5 V
TR(os)	01,03,04		+50 mV referenced to GND
	02		+250 mV referenced to GND
	05,06		+50 mV referenced to 5 V
SR(+)	01,03,04		-5 V to +5 V step
	02		-1 V to +1 V step
	05,06		+5 V to +15 V step
SR(-)	01,03,04		+5 V to -5 V step
	02		+1 V to -1 V step
	05,06		+15 V to +5 V step

FIGURE 4. <u>Test circuit and waveform for transient response</u> – Continued.

MIL-M-38510/110C

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

																Device types	types			
Symbol MIL-STD Test Adapter pin numbers	MIL-STD Test Adapter pin numbers	Test Adapter pin numbers							Energized					01	01, 02	0	03	04	4	Unit
-883 no.	no.							_	relays <u>2</u> /	Ž	Measured pins	ns	Equations 3/	ij	Limits	Lir	Limits	Lin	Limits	
method 1 2 3 4 5	1 2 3 4	1 2 3 4	2 3 4	3 4	4		2			No.	Value	Unit		Min	Мах	Min	Мах	Min	Max	
V _{IO} 4001 1 4/ 35 V -5 V	1 <u>4</u> / 35 V -5 V	4/ 35 V -5 V	-5 V		-15 V	-15 V			None	5	E1	^	VIO = E1		∓5		∓3		∓2	/m
" 2 <u>4</u> / 5 V -35 V 15 V	2 <u>4</u> / 5 V -35 V	<u>4</u> / 5 V -35 V	-35 V		15 V	15 V			2		E2	3	VIO = E2		9∓		±3		1 2	*
" $3 \ \underline{4/5}/$ $20 \ V$ -20 V GND	3 <u>4</u> / <u>5</u> / 20 V -20 V	<u>4</u> /5/ 20 V -20 V	-20 V		GND	GND			4		E3	*	VIO = E3		9∓		+3		+ 2	3
" 4 <u>4</u> / 5 V -5 V GND	4 <u>4</u> / 5 V -5 V	4 5v -5v	-5 V		GND	GND			ä		E4	*	VIO = E4		9∓		±3		+ 5	*
" 5 35 V -5 V	5 35 \ -5 \	35 V5 V	-5 V		-15 V	-15 V			K5, K6		E5	:	I ₁ O = 50 (E ₁ – E ₅)		+25		±30		±75	PA
. 6 5 7 -35 7	5 V -35 V	5 V -35 V	-35 V		15 V	15 V	J		3		E6		I ₁ O = 50 (E ₂ – E ₆)		+25		±30		±75	:
" 7 20 V -20 V GND	20 V20 V	20 V20 V	-20 V		GND	GND			ä		E7	:	I ₁ O = 50 (E ₃ – E ₇)		±25		±30		±75	*
8 5 V -5 V GND	8 5 \ -5 \	5 V5 V	-5 V		GND	GND			3		E8		IIO = 50 (E4 – E8)		+25		∓30		±75	3
+I _{IB} " 9 35 V -5 V	9 35 \ -5 \	35 V -5 V	-5 V		-15 V	-15 V			K5		E9	3	+llB = 50 (E1 –E9)	-0.1	100	-200	+0.1	-250	+0.1	Ą
10 5 V -35 V 15 V	5 V -35 V	5 V -35 V	-35 V		15 V	15 V			ä		E10	3	+IIB = 50 (E2 –E10)	-0.1	100	-200	+0.1	-250	+0.1	2
" 11 20 V -20 V GND	20 V20 V	20 V20 V	-20 V		GND	GND			4		E11	3	+IIB = 50 (E3 –E11)	-0.1	100	-200	+0.1	-250	+0.1	3
" 12 5 V -5 V GND	5 V 5 V	5 V 5 V	-5 V		GND	GND			2		E12		+IIB = 50 (E4 –E12)	-0.1	100	-200	+0.1	-250	+0.1	ä
-IIB 13 35 V -5 V -15 V	13 35 \ -5 \	35 V5 V	-5 V		-15 V	-15 V	J		, Y		E13	3	-IIB = 50 (E13 –E1)	-0.1	100	-200	+0.1	-250	+0.1	ΡΑ
14 5 V -35 V 15 V	14 5 V -35 V	5 V -35 V	-35 V		15 V	15 V			3		E14	3	-IIB = 50 (E14 –E2)	-0.1	100	-200	+0.1	-250	+0.1	3
" 15 20 V20 V GND	20 V20 V	20 V20 V	-20 V		GND	GND			3		E15	3	-IIB = 50 (E15 –E3)	-0.1	100	-200	+0.1	-250	+0.1	3
16 5 V5 V GND	5 V5 V	5 V5 V	-5 V		GND	GND			2		E16	3	-IIB = 50 (E16 –E4)	-0.1	100	-200	+0.1	-250	+0.1	*
+PSRR 4003 17 10 V -20 V GND	17 10 V -20 V	10 V -20 V	-20 V		GND	GND			None		E17	3	+PSRR = (E3 – E17) x 100		∓100		±100		∓100	MVΛ
-PSRR 4003 18 20 V -10 V GND	18 20 \ -10 \	20 V10 V	-10 V		GND	GND	l		None		E18	3	-PSRR = (E3 – E18) x 100		±100		±100		∓100	μV/V
CMR 4003 19 <u>4/</u> Calculate value using data from tests 1 and 2	19 4/		Calculate value using data from tests 1 a	e value using data from tests 1 a	ing data from tests 1 a	rom tests 1 a	_ a	nd 2			•		CMR = 20 log $ 3 \times 10^4 / E1 - E2 $	92		92		92		æ
loS(+) 3011 20 <u>6</u> / 15 V -15 V GND -10 V	20 <u>6/</u> 15 V -15 V GND	<u>6</u> / 15 V -15 V GND	-15 V GND	GND		-10 V	Į		None	3	7	A W	IOS(+) = I1	-55		-80		-80		Ψ
IOS(-) 3011 21 <u>6</u> / 15 V -15 V GND 10 V	21 <u>6</u> / 15 V -15 V GND	<u>6</u> / 15 V -15 V GND	-15 V GND	GND		10 V			2	3	[2	3	IOS(-) = 12		55		80		80	3
I _{CC} 3005 22 <u>7</u> / 15 V -15 V	22 <u>7</u> / 15 V	<u>7</u> / 15 V		-15 V					z	2	3	ä	ICC = 13		3.6		7		11	3
VIO 4001 23 4/ 35 V -5 V -15 V	23 <u>4/</u> 35 V -5 V	<u>4</u> / 35 V -5 V	-5 V		-15 V	-15 V			*	5	E19	>	VIO = E19		9∓		+ 5		9	٦ ٧
24 4/ 5 V -35 V 15	24 <u>4</u> / 5 V -35 V	<u>4</u> 5 V -35 V	-35 V		15	15			*	5	E20	3	VIO = E20		9∓		7		9	*
" 25 <u>4</u> / <u>5</u> / 20 V -20 V GND	25 <u>4</u> / <u>5</u> / 20 V -20 V	<u>4</u> / <u>5</u> / 20 V -20 V	-20 V		GND	GND			3	5	E21	3	VIO = E21		9∓		7		9	3
" 26 <u>4</u> / 5 V -5 V GND	26 <u>4</u> / 5 V5 V	5 V5 V	-5 V		GND	GND	l		2	5	E22	ä	VIO = E22		9=		±5		9	33

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

_			_			1										Device types	types			
Subgroup	Symbol	Symbol MIL-STD	Test		Adapte	Adapter pin numbers	bers	Ш	Energized					01,	01, 02	03		04		Unit
		-883	no.						relays <u>2</u> /	Me	Measured pins	SI	Equations 3/	Lin	Limits	Limits	iits	Limits	its	
		method		1	2	3	4	5		No.	Value	Unit		Min	Мах	Min	Max	Min	Max	
2	/ OI/V	4001	27	- ΤΔ / ΟΙVΔ	/	O (Test 2	= (VIO (Test 25 – VIO (Test 3)) / 100°C	est 3)) / 1	2∘00						±25		±20		+25	μV/′°C
TA =+125°C	ΔΤ	3																		
	Oll	3	28	35 V	Λ 9-		-15 V		K5, K6	2	E23	>	IIO = 50 (E19 – E23)		±25		∓30		±75	ν
		*	29	2 V	Λ 9ε-		15 V		3	*	E24	*	IIO = 50 (E20 – E24)		±25		∓30		±75	3
		3	30	20 V	-20 V		GND		3	3	E25	3	IIO = 50 (E21 – E25)		±25		±30		±75	3
		3	31	2 \	-5 V		GND		3	3	E26	3	IIO = 50 (E22 – E26)		±25		±30		±75	*
	ΤΔ/ΟΙΙΔ	3	32 <u>8</u> /	ΔVIC	$\Delta V_{IO} / \Delta T = (I_{IG})$	O (Test 30	= (I _{IO} (Test 30) – I _{IO} (Test 7)) / 100°C	st 7)) / 1	200€						+200		±200		∓200	pA/°C
	8Ij+	3	33	35 V	^ S-		-15 V		K5	2	E27	>	+IIB = 50 (E19 –E27)	-0.1	100	-200	+0.1	-250	+0.1	nA
		3	34	5 V	-35 V		15 V		3	:	E28	:	+IIB = 50 (E20 –E28)	-0.1	100	-200	+0.1	-250	+0.1	*
		3	35	20 V	-20 V		GND		3	3	E29	3	+IIB = 50 (E21 –E29)	-0.1	100	-200	+0.1	-250	+0.1	3
		:	36	5 V	∧ 9 -		GND		ä	3	E30	3	+IIB = 50 (E22 –E30)	-0.1	100	-200	+0.1	-250	+0.1	,
	-lıB	3	37	35 V	-5 V		-15 V		8	3	E31	*	-IIB = 50 (E31 –E19)	-0.1	100	-200	+0.1	-250	+0.1	ν
		3	38	5 V	-35 V		15 V		3	3	E32	*	-IIB = 50 (E32 –E20)	-0.1	100	-200	+0.1	-250	+0.1	3
		3	39	20 V	-20 V		GND		3	3	E33	3	-IIB = 50 (E33 –E21)	-0.1	100	-200	+0.1	-250	+0.1	3
		ä	40	5 V	-5 V		GND		z	3	E34		-IIB = 50 (E34 –E22)	-0.1	100	-200	+0.1	-250	+0.1	2
	+PSRR	4003	41	10 V	-20 V		GND		None	3	E35	z	+PSRR = (E21 – E35) x 100		±100		±100		∓100	μV/V
	-PSRR	4003	42	20 V	-10 V		GND		None	3	E36	ä	-PSRR = (E21 – E36) × 100		±100		±100		∓100	μV/V
	CMR	4003	43 4/	Calculat	e value us	ing data f	Calculate value using data from tests 23 and 24.	23 and 24	,				CMR = 20 log $ 3 \times 10^4 / E19 - E20 $	76		92		76		фВ
	los(+)	3011	44 <u>6</u> /	15 V	-15 V	GND	-10 V		None	က	4	МA	IOS(+) = 14	-55		-80		-80		ΑM
	los(-)	3011	45 <u>6</u> /	15 V	-15 V	GND	10 V			က	5	3	lOS(-) = l5		55		80		80	3
	22	3005	46 <u>7</u> /	15 V	-15 V					2	9	3	ICC = 16		3.6		7		11	3
2	ΟlΛ	4001	47 4/	35 V	-5		-15 V		None	2	E37	>	VIO = E37		9∓		7		9#	>E
TA =		Į.	48 4/	5 V	-35 V		15		[5	E38	3	VIO = E38		9#		7		9#	3
-55°C			49 4/	20 V	-20 V		GND			2	E39	3	VIO = E39		9#		7		9+	3
			50 4/	5 V	-5 V		GND			2	E40	ä	VIO = E40		9#		7		9∓	3

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

															Device types	types			
Subgroup		Symbol MIL-STD	Test		Adapter	Adapter pin numbers	bers	Energized					01,	01, 02	03	3	04	4	Unit
		-883	no.					relays <u>2</u> /	2	Measured pins	ins	Equations 3/	Πİ	Limits	Limits	nits	Limits	iits	
		method		1	2	3	4 5		No.	Value	Unit		Min	Max	Min	Max	Min	Мах	
ю	/OIΛΔ	4001	51 <u>8</u> /	∆VIO / ∆T		O (Test	= (VIO (Test 3 – VIO (Test 49)) / 80°C)) / 80°C						+25		±20		±25	μV/°C
TA =-55°C	ΔT																		3
	임	3	52	35 V	-5 V		-15 V	K5, K6	2	E41	>	IIO = 50 (E37 – E41)		9 2∓		±75		±150	NA
		"	53	5 V	-35 V		15 V	3	3	E42	3	IIO = 50 (E38 – E42)		9 2∓		±75		±150	4
		3	54	20 V	-20 V		GND	*	3	E43	3	IIO = 50 (E39 – E43)		9 2∓		±75		±150	4
		ä	55	5 V	-5 V		GND	я	n	E44	29	IIO = 50 (E40 – E44)		∓75		±75		±150	ä
	ΔΙΟ/ΔΤ	3	56 <u>8</u> /	ΔVIC	ll) = T∆ / C	O (Test 7	∆VIO / ∆T = (IIO (Test 7 – IIO (Test 54)) / 80°C) / 80°C						∓400		∓200		±1000	pA/°C
	<u>=</u>	3	57	35 V	-5 V		-15 V	K5	2	E45	>	+I ₁ B = 50 (E ₃₇ –E ₄₅)	-0.1	325	-325	+0.1	-400	+0.1	пА
		*	58	5 V	-35 V		15 V	:	:	E46	3	+IIB = 50 (E38 –E46)	-0.1	325	-325	+0.1	-400	+0.1	*
		3	59	20 V	-20 V		GND	3	3	E47	3	+IIB = 50 (E39 –E47)	-0.1	325	-325	+0.1	-400	+0.1	4
		3	60	5 V	-5 V		GND	3	:	E48	3	+I ₁ B = 50 (E ₄₀ –E ₄₈)	-0.1	325	-325	+0.1	-400	+0.1	2
	-IIB	3	61	35 V	-5 V		-15 V	K6	*	E49	3	-IIB = 50 (E49 –E37)	-0.1	325	-325	+0.1	-400	+0.1	νγ
		3	62	5 V	-35 V		15 V	:	3	E50	3	-IIB = 50 (E50 –E38)	-0.1	325	-325	+0.1	-400	+0.1	3
		3	63	20 V	-20 V		GND	=	3	E51	3	-IIB = 50 (E51 –E39)	-0.1	325	-325	+0.1	-400	+0.1	3
		¥	64	5 V	-5 V		GND	2	:	E52	3	-IIB = 50 (E52 –E40)	-0.1	325	-325	+0.1	-400	+0.1	ä
	+PSRR	4003	65	10 V	-20 V		GND	None	3	E53	3	+PSRR = (E39 – E53) × 100		±100		±100		±100	μV/V
	-PSRR	4003	66	20 V	-10 V		GND	None	3	E54	"	-PSRR = (E39 – E54) x 100		±100		±100		±100	мνм
	CMR	4003	67 4/	Calculate	e value usi	ng data f	Calculate value using data from tests 47 and 48	d 48				CMR = 20 log $ 3 \times 10^4 / E37 - E38 $	92		76		76		dB
	lOS(+)	3011	68 <u>6</u> /	15 V	-15 V	GND	-10 V	None	3	71	mA	10S(+) = 17	92-		-80		-80		мĄ
	(-)SO _I	3011	69 <u>6</u> /	15 V	-15 V	GND	10 V	*	3	18	3	lOS(-) = 18		75		80		80	*
	ICC	3005	70 <u>7</u> /	15 V	-15 V			3	2	61	n	ICC = 19		4.5		6		13	3
4	+V0P	4004	71	20 V	-20 V		-20 V	% 8	က	(E0)1	>	+VOP = (E0)1	+16		+16		+16		>
= AT	-V0P	3	72	20 V	-20 V		20 V	8 8	က	(E0)2	3	-VOP = (E0)2		-16		-16		-16	3
+25°C	+VOP	3	73	20 V	-20 V		-20 V	K7	8	(E0)3	3	+VOP = (E0)3	+15		+15		+15		3
	VOP	3	74	20 V	-20 V		20 V	K7	က	(E0)4	3	-VOP = (E0)4		-15		-15		-15	ä

MIL-M-38510/110C

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

	Unit			//m//	3	3	:	3	3	*	3	>	3	:	×	//m//	3	2	3	*	3	з	3	>	3	3	2
	_	its	Мах										-16		-15										-16		-15
	04	Limits	Min	20	20	90	90	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
types		its	Max										-16		-15										-16		-15
Device types	03	Limits	Min	20	20	90	50	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
-	02	its	Max										-16		-15										-16		-15
	01, 02	Limits	Min	50	50	20	50	10		10		+16		+15		25	25	25	25	10		10		+16		+15	
		Equations 3/		AVS(+) = 15/(E3 – E55)	AVS(+) = 15/(E3 – E56)	AVS(-) = 15/(E57 – E3)	AVS(-) = 15/(E58 – E3)	$AVS = 4/(E_{60} - E_{59})$		AVS = 4/(E62 - E61)		+VOP = (E0)5	-VOP = (E0)6	+VOP = (E0)7	-VOP = (E0)8	AVS(+) = 15/(E21 - E63)	AVS(+) = 15/(E21 - E64)	AVS(-) = 15/(E65 – E21)	AVS(-) = 15/(E66 - E21)	Avs = 4/(E68 – E67)		Avs = 4/(E70 – E69)		+VOP = (E0)9	-VOP = (E0)10	+VOP = (E0)11	-VOP = (E0)12
		ins	Unit	>	3	3	:	3	3	3	ä	3	3	:	3	3	3	3	ä	3	3	3	3	3	3	3	ä
		Measured pins	Value	E55	E56	E57	E58	E59	E60	E61	E62	(E0)5	(E0)6	(E0)7	(E0)8	E63	E64	E65	E66	E67	E68	E69	E70	(E0)9	(E0)10	(E0)11	(E0)12
		Ň	No.	5	3	3	*	3	3	3	ä	3	3	в	3	5	3	3	ä	3	ä	ä	3	3	3	в	3
	Energized	relays <u>2</u> /		K8	K7	K8	K7	K8	K8	K7	K7	K8	K8	K7	K7	K8	K7	K8	K7	K8	K8	K7	K7	K8	K8	K7	K7
			5																								
	nbers		4	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 V	-20 V	20 V	-20 V	20 V	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 V	-20 V	20 V	-20 V	-20 V
	Adapter pin numbers		3																								
	Adapte		2	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 V	-20 V	-20 V	-20 V	-20 V
			1	20 V	20 V	20 V	20 V	5 V	5 V	5 V	5 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	5 V	5 V	5 V	5 V	20 V	20 V	20 V	20 V
	Test	no.		75 <u>5</u> /	76 5/	77 <u>5</u> /	78 <u>5</u> /	79		80		81	82	83	84	85 <u>5</u> /	86 <u>5</u> /	87 <u>5</u> /	88 <u>5</u> /	89		06		91	92	93	94
	MIL-STD	-883	method	4004	3	: :	*	2	3	3	3	*	ä	=	ä	=	*	=	*	*	3	ı z	3	*	*	3	×
	Symbol			AVS(+)	AVS(+)	AVS(-)	AVS(-)	Avs				+VOP	-VOP	+VOP	-Vop	AVS(+)	AVS(+)	AVS(-)	AVS(-)	AVS				+VOP	-VOP	+VOP	-Vop
	Subgroup			4	TA =+25°C	l						2	TA =+125°C	l			l							9	TA =	-55°C	

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

	Unit			//m//	*	*	3	3	3	3	3	μVrms	μVpk	ВВ	3	3	2	*	3	3	3	3	*	3	3	3	*	3	*	3	3
			Max									ъ т	20																		
	04	Limits	Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
s					2	.,	2	_					-	8	8	8	ω	ω	ω	ω		8	ω	ω	ω	ω	ω	ω	ω	ω	8
Device types	03	Limits	Max									5	20																		
De			Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
	01, 02	Limits	Max									15	40																		
	0	: <u> </u>	Min	25	25	25	25	10		10				80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80	80
		Equations 3/		AVS(+) = 15/(E39 – E71)	AVS(+) = 15/(E39 - E72)	AVS(-) = 15/(E73 – E39)	AVS(-) = 15/(E74 - E39)	AVS = 4/(E76 - E75)		AVS = 4/(E78 - E77)		NI(BB) = (E0)13	NI(PC) = (E0)14	CS = 20 log	$ 2 \times 10^4 / E79 - E80 $	CS = 20 log	2 × 10	CS = 20 log	2 x 10 ⁴ / E83 – E84	CS = 20 log	$ 2 \times 10^4 / E85 - E86 $	CS = 20 log	2 × 10	CS = 20 log	$ 2 \times 10^4 / \text{E89} - \text{E90} $	CS = 20 log	2 × 10	CS = 20 log	$ 2 \times 10^4 / E93 - E94 $	CS = 20 log	2 × 10
		ns	Unit	>	:	3	3	3	*	:	3	mVrms	mVpk	>	3	*	3	3	3	3	*	3	:	ä	3	*	ä	3	3	3	"
		Measured pins	Value	E71	E72	E73	E74	E75	E76	E77	E78	(E0)13	(E0)14	E79	E80	E81	E82	E83	E84	E85	E86	E87	E88	E89	E90	E91	E92	E93	E94	E95	E96
		Me	No.	2	3	3	*	3	*	3	×	က	ю	2	*	*	3	3	2	3	3	3	3	3	3	*	3	3	*	3	×
	Energized	relays 2/		K8	K7	K8	K7	K8	K8	K7	K7	K10, K11	K5, K6, K10, K11	See fig. 3	3	3	3	ä	3	3	3	3	3	ä	3	3	z	ä	ä	z	3
			2																												
	ers		4	-15 V	-15 V	15 V	15 V	-2 V	2 V	-2 V	2 \	GND	3	"	,	"	3	3	3	3	3	3	3	ä	3	*	3	33	ä	ä	3
	Adapter pin numbers		3											11/	12/	11/	12/	11/	12/	17	<u>12</u> /	11/	12/	11/	12/	11/	12/	11/	12/	11/	12/
	Adapter		2	-20 V	-20 V	-20 V	-20 V	-5 V	-5 V	-5 V	-5 <	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V
		•	1	- 20 V	20 V	20 V	20 V	5 V	5 V	5 V	2 \	20 V	20 V	20 V	20 V	20 V	- 70 V	- 70 V	20 V	20 V	20 V	20 V	20 V	20 V	- 70 V	20 V	20 V	20 V	20 V	20 V	20 V
									u)	/6I	4)	20/ 2			2		Ñ		2		2		2		2		2	l	2		2
	T Test	no.	р	96	96	97	98	66		100		101	102	103		104		105		106		107		108		109		110		111	
	MIL-ST	-883	method	4004	3	*	3	3	3	3	3	1																			
	Symbol MIL-STD			AVS(+)	AVS(+)	AVS(-)	AVS(-)	AVS				NI(BB)	NI(PC)	SO																	
	Subgroup			9	TA =-55°C							7	TA =+25°C																		

TABLE III. Group A inspection for device types 01, 02, 03, and 04. 1/

E III	. <u> </u>	100	ip F	11113	pec	lion	101 (devi	JE LY	pes	01, 02	2, 03,	and 04	<u>4</u> . <u>1</u> /
	Unit			ВВ	:	:	3	3	3	sm	%	N/μs	ν/μs	
	4	Limits	Max							0.3	20			
	04	Lin	Min	80	80	80	80	80	80			0.6	0.6	
types		ts	Max							0.2	35			
Device types	03	Limits	Min	80	80	80	80	80	80			0.8	0.8	
	12	ts	Max							1.0	25			
	01, 02	Limits	Min	80	80	80	80	80	80			/6	/6	
		Equations 3/		CS = 20 log	2 × 10	CS = 20 log	2 × 10	CS = 20 log	2 × 10	(Waveform 1) TR(t _r) = ∆t	(Waveform 1) TR(OS) – 100 (∆VO/VO)	(Waveform 2) SR(+) = $VO/\Delta t$	(Waveform 3) SR(-) = $\Delta VO/\Delta t$	Same tests, terminal conditions and limits as subgroup7, tests 115 through 118 except TA = 125°C and TA = -55°C.
		8	Unit	>	3	3	*	"	**	sri	>	V; µs	V; µs	cept TA =
		Measured pins	Value	E97	E98	E99	E100	E101	E102	Δt	VO;ΔVO	ΔVO; Δt	ΔVO; Δt	ırough 118 e)
		V	No.	2	3	3	*	*	*	3	3	"	2	sts 115 th
	Energized	relays 2/		See fig. 3	3	3	3	3	*	See fig. 4	z	3	3	bgroup7, tes
			5							TUO				nits as su
	pers		4	GND	*	*	"	n	"	2	n	"	n	ons and lii
	Adapter pin numbers		3	11/	12/	11/	12/	11/	12/	Z				al conditic
	Adapte		2	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	-20 V	ts, termin
			1	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	20 V	Same tes
	Test	90.		112		113		114		115	116	117	118	119 to
	MIL-STD	-883	method					<u> </u>						
	Symbol			SS						TR(t _r)	TR(os)	SR(+)	SR(-)	
	Subgroup			7	TA =+25°C									∞

TABLE III. Group A inspection for device types 05 and 06. 1/

1																Device types	types		
Marie Mari	Subgroup		MIL-STD			Adapter	pin num	bers		Energized					ő	10	90		Unit
VADIAL METERS 1 1 2 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0			-883	no.						relays <u>2</u> /	Me	asured pin	s		Lim	its	Lim	ts	
VD 4001 14 g 30 V GND 14 V None 6 E1 V VOD=E1 15 S 15			method		-	2	3	4	5		No.	Value	Unit		Min	Max	Min	Max	
1	1	ΟlΛ	4001	1 4/	30 V	GND		-15 V		None	2	E1	^	VIO = E1		+ 5		±2	Λm
1	TA =				2 \	-28 V		13 V		3	*	E2	3	VIO = E2		+ 2		±2	3
1	+25°C				2 \	GND		-1.4 V		3	3	E3	3	VIO = E3		+ 2		±2	3
10 10 10 10 10 10 10 10					2.5 V	-2.5 V		1.1 V		3	3	E4	=	VIO = E4		+ 2		+2	*
High High High High High High High High		OII		2	30 V	GND		-15 V		K5, K6	3	E5	*	IIO = 10 ⁶ (E1 – E5)/RS		∓30		∓10	νγ
HIND HIND HIND HIND HIND HIND HIND HIND				9	2 V	-28 V		13 V		3	3	E6	*	E2		∓30		∓10	3
HIND HIND HIND HIND HIND HIND HIND HIND				7	5 V	GND		-1.4 V		3	3	E7	*	IIO = 10 ⁶ (E ₃ – E ₇) /R _S		∓30		110	:
High Fig. Fig. High				8	2.5 V	-2.5 V		1.1 V		*	3	E8	*	IIO = 10 ⁶ (E4 – E8) /RS		∓30		±10	"
Hand Hand Hand Hand Hand Hand Hand Hand		+IIB		6	30 V	GND		-15 V		K5	3	E9	*	+I _{IB} = 10 ⁶ (E ₁ –E ₉) /R _S	-150	+0.1	-50	+0.1	νγ
11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 5 \ 6 \ 6 \ 11 6 \ 6				10	2 V	-28 V		13 V		*	*	E10	3	+IIB = 10 ⁶ (E2 –E10) /RS	-150	+0.1	-50	+0.1	*
Hand Hand Hand Hand Hand Hand Hand Hand				11	5 V	GND		-1.4 V		*	*	E11	,,	+IIB = 10 ⁶ (E3 –E11) /RS	-150	+0.1	-50	+0.1	3
-IIB - IIB - IIB - III - III - III - III - III - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIII - IIIII - IIII - IIIII - IIIII - IIIII - IIII - IIIII - IIII - IIII - IIII - IIII -				12	2.5 V	-2.5 V		1.1 V		*	*	E12	3	+IIB = 10 ⁶ (E4 –E12) /RS	-150	+0.1	-50	+0.1	,
HASRR 4003 17 50 GND 1.14 None 1.05(H)		-IB		13	30 V	GND		-15 V		, K	*	E13	2	-IIB = 10 ⁶ (E13 –E1) /RS	-150	+0.1	-50	+0.1	nA
+PSRR 403 15 5 V GND -14 V " E16 " -118 = 10 ⁶ (E15 - E3)/Rg -150 +0.1 -50 +0.1 +PSRR 4403 17 30 V GND -1.4 V None " E17 " -118 = 10 ⁶ (E16 - E4)/Rg -150 +0.1 -50 +0.1 CMR 403 17 30 V GND -1.4 V None " E17 " -198 = 10 ⁶ (E16 - E4)/Rg -150 +0.1 -50 +0.1 CMR 403 18 4 GND -1.4 V None " E17 " -198 = 10 ⁶ (E16 - E4)/Rg -150 +0.1 -50 +0.1 LOSK 403 18 4 GND -1.4 V None 3 11 mA LOC=12 -70 70 70 -70 LOSK 300 GND -15 V None 2 12 MA LOC=12 70 77 70 70 10C				14	2 V	-28 V		13 V		*	3	E14	*	-IIB = 10 ⁶ (E14 –E2) /RS	-150	+0.1	-50	+0.1	3
+PSRR 4003 17 30 V GND -1.4 V None " E16 " -IB= 10 ⁶ (E16-E4)/RS -150 +0.1 -50 -50 <				15	5 V	GND		-1.4 V		:	×	E15	:	-I _{IB} = 10 ⁶ (E ₁₅ –E ₃) /R _S	-150	+0.1	-50	+0.1	:
HPSRR 4003 17 30 V GND				16	2.5V	-2.5 V		1.1 V		3	*	E16		-IIB = 10 ⁶ (E16 –E4) /RS	-150	+0.1	-50	+0.1	2
CMR 4003 18 4/2 Calculate value using data from tests 1 and 2.5 v GND 4001 21 4/2 so v GND 6ND 700 6ND		+PSRR	4003	17	30 V	GND		-1.4 V		None	*	E17	3	+PSRR = (E17 – E18)		∓100		∓100	μV/V
CMR 4003 18 4/b Calculate value using data from tests 1 and 2 Annotes 2 1,1 mA COMR = 20 log 76					2 \	GND		-1.4 V		None	3	E18	3	× 40					3
IOS(+) 3011 19 £/s 30 V GND CS V None 3 11 mA IOS(+)=11 -70 -70 -70 I _{CC} 3005 20 Z/s 30 V GND -15 V None 2 12 mA I _{CC} =12 3 7 3 3 3 V _{IO} 4001 21 ½ 30 V GND -15 V None 5 E19 V V _{IO} =E19 3 4 4 " 22 ½ 2 V -28 V 13 V " E20 " V _{IO} =E29 4 4 4 " 23 ½ 5 V GND -1.4 V " E21 " V _{IO} =E29 4 7 4 " 24 ½ 2.5 V -2.5 V 1.1 V " E21 " V _{IO} =E22 17 " 4		CMR	4003		Calcula	ite value us	sing data	from tests	s 1 and	2				CMR = 20 log $ 2.8 \times 10^4 / E1 - E2 $	76		76		ф
ICC 3005 20 I/2 30 V GND -15 V None 2 I2 mA ICC = I2 3 3 3 VIO 4001 21 I/2 30 V GND -15 V None 5 E19 V VIO = E19 ±7 ±4 " 22 I/2 2 V -28 V 13 V " E20 " VIO = E20 ±7 ±4 " 23 I/2 5 V GND -1.4 V " E21 " VIO = E21 ±7 ±4 " 24 I/2 2.5 V -2.5 V 1.1 V " E22 " VIO = E22 ±7 ±4		(+)SO ₍₊₎	3011		30 V	GND	GND	-25 V		None	8	7	mA	lOS(+) = l1	-70		-70		mA
VIO 4001 21 4/2 30 V GND -15 V None 5 E19 V VIO=E19 ±7 ±4 " 22 4/2 2 V -28 V 13 V " E20 " VIO=E20 ±7 ±4 " 23 4/2 5 V GND -14 V " E21 " VIO=E21 ±7 ±4 " 24 4/2 2.5 V -2.5 V 1.1 V " " E22 " VIO=E22 ±7 ±4		<u>8</u>	3005	20 <u>7</u> /	30 V	GND				None	2	12	mA	ICC = 12		က		က	mA
		οlν	4001	21 4/	30 V	GND		-15 V		None	2	E19	>	VIO = E19		7±		4+	/m
" 23 <u>4</u> / 5 V GND -1.4 V " " E21 " VIO=E21 ±7 ±4 " 24 <u>4</u> / 2.5 V -2.5 V 1.1 V " " E22 " VIO=E22 ±7 ±4		•	*	22 4/	2 V	-28 V		13 V		3	3	E20	3	VIO = E20		7=		+ +	3
" 24 4/ 2.5 V -2.5 V 1.1 V " E22 " VIO=E22 ±7	2		3	23 4/	5 V	GND		-1.4 V		*	3	E21	:	VIO = E21		7±		+ 4	3
	TA =+125°C		*	24 4/	2.5 V	-2.5 V		1.1 V		3	ä	E22	ž	VIO = E22		7±		+ 4	ž

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

															Device types	types		
Subgroup	Symbol	MIL-STD	Test		Adapter	Adapter pin numbers	bers		Energized					90	5	ŏ	90	Unit
		-883							relays <u>2</u> /	Me	Measured pins	ns	Equations 3/	Limits	nits	Lin	Limits	
		method		-	2	3	4	2	•	No.	Value	Unit		Min	Мах	Min	Мах	
2	∆VIO / ∆T	4001	25	OIVA	∆VIO / ∆T = (VIO (Test 23 – VIO (Test 3)) / 100°C	O (Test 2	73 – VIO (1	Test 3)) /	100°C						±30		∓30	μV/′°C
TA =+125°C	OII	*	26	30 V	GND		-15 V		K5, K6	5	E23	^	$I_{10} = 10^{6} (E_{19} - E_{23})/R_{S}$		∓30		±10	hu
		3	27	2 V	-28 V		13 V		3	3	E24	3	IIO = 10 ⁶ (E ₂₀ – E ₂₄)/ R _S		±30		±10	3
		*	28	5 V	GND		-1.4 V		*	3	E25	:	IIO = 10 ⁶ (E21 – E25)/ RS		±30		±10	*
		3	29	2.5 V	-2.5 V		1.1 V		3	3	E26	*	$I_{10} = 10^{6} (E_{22} - E_{26})/R_{S}$		∓30		±10	n
	ΔΙΙΟ/ΔΤ	3	30 <u>8</u> /	OllA	∆lıO /∆T = (lıO (Test 28 – lıO (Test 7)) / 100°C) (Test 2	8 – IJO (Te	est 7)) / 1	೦್೦೦						±400		±400	pA/°C
	+IIB	3	31	30 V	GNĐ		-15 V		K5	5	E27	^	$+IIB = 10^{6} (E_{19} - E_{27})/RS$	-150	+0.1	-50	+0.1	hu
		*	32	2 V	-28 V		13 V		*	3	E28	3	$+IIB = 10^{6} (E_{20} - E_{28})/RS$	-150	+0.1	-50	+0.1	*
		3	33	5 V	-GND		-1.4 V		×		E29		$+IIB = 10^{6} (E_{21} - E_{29})/RS$	-150	+0.1	-50	+0.1	2
		3	34	2.5 V	-2.5 V		1.1 V		*	3	E30	3	$+IIB = 10^{6} (E_{22} - E_{30})/RS$	-150	+0.1	-50	+0.1	**
	- HB	3	35	30 V	GND		-15 V		9		E31		-IIB = 10 ⁶ (E31 –E19)/ RS	-150	+0.1	-50	+0.1	hA
		3	36	2 \	-28 V		13 V		¥	3	E32	3	-IIB = 10^6 (E32 –E20)/ RS	-150	+0.1	-50	+0.1	3
		3	37	5 V	GND		-1.4 V		3	3	E33	3	-IIB = 10^6 (E33 –E21)/ RS	-150	+0.1	-50	+0.1	3
		y	38	2.5 V	-2.5 V		1.1 V		**	3	E34	3	-IIB = 10^6 (E34 –E22)/ RS	-150	+0.1	-50	+0.1	n
	+PSRR	4003	39	30 V	GND		-1.4 V		None	3	E35	3	+PSRR = (E35 – E36)		±100		±100	ΛVμ
		¥		5 V	GND		-1.4 V		None	3	E36	ä	× 40					*
	CMR	4003	40 4/	Calculate	Calculate value using data from tests 21 and 22.	ing data f	from tests	21 and 2	5.				$CMR = 20 log 2.8 \times 10^{4} / E19 - E20 $	92		92		dВ
	lOS(+)	3011	41 <u>6</u> /	30 V	GND	GND	-25 V		None	3	<u>8</u>	mA	lOS(+) = l3	-70		-70		mA
	Icc	3005	42 7/	30 V	GND				None	2	4	mA	ICC = 14		3		3	mA
7	ΟlΛ	4001	43 <u>4</u> /	30 V	GND		-15 V		None	2	E37	>	VIO = E37		7		∓4	/m
TA =			44 4/	2 V	-28 V		13		3	3	E38	3	VIO = E38		7		∓4	¥
+125°C			45 4/	5 V	GND		-1.4 V		*	3	E39	3	VIO = E39		7		∓4	3
			46 4/	2.5 V	-2.5		1.1 V		79	ä	E40	ä	VIO = E40		7=		+4	39
	∆VIO / ∆T		47 <u>8</u> /	ΔVIC	$\Delta V_{IO} / \Delta T = (V_{IO} (Test 3 - V_{IO} (Test 45)) / 80^{\circ}C$	IO (Test	3 – VIO (T	est 45))/	.80°C						∓30		±30	μV/°C

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

MIL-STD Test	Adapter pin numbers	numbers								Device	Device types		
50 5 V 50 5 S 50	. 7			Energized					90		90		Unit
1 48 30 49 2 V 50 50 5 V 50 50 5 V 50 50 50 50 50 50 50 50 50 50 50 50 50				relays <u>2</u> /	Me	Measured pins	SI	Equations <u>3</u> /	Limits	ıts	Limits	23	
49 49 2 V 50 54 2 V 51 2.5 18 55 5 V 52 8 55 5 V 55 50 50 50 50 V 61 30 V		3 4	2		o N	Value	Unit		Min	Мах	Min	Max	
50 50 50 50 50 50 50 50 50 50 50 50 50 5	GND	-15 V		K5, K6	2	E41	>	I ₁ O = 10 ⁶ (E ₃ 7 – E ₄₁)/R _S		±75		+30	PA
50 51 52 82 83 53 54 2 V 54 2 V 54 2 V 54 54 54 54 57 57 50 60 61 61 61 61 61 61 61 61 61 61	-28 V	13 V		3	3	E42	3	IIO = 10 ⁶ (E38 – E42) /RS		±75		∓30	3
52 8/ 52 8/ 53 30V 54 2 V 56 2.5' 56 2.5' 60 2.5' 61 30V	GND	-1.4 V		3	3	E43	3	liO = 10 ⁶ (E39 – E43) /RS		±75		±30	3
52 8/ 54 2 v 55 5 5 5 5 5 5 6 6 5 6 6 6 6 1 2 5 7 30 v 59 5 v 60 6 1 30 v 50 5 v 6 6 1 30 v	-2.5 V	1.1 V		"	,,	E44	,	$I_{IO} = 10^6 (E_{40} - E_{44}) /R_{S}$		±75		+30	3
55 54 55 56 56 60 60 60 60	∆I ₁ O / ∆T = (I ₁ O (Test 50 – I ₁ O (Test 7)) / 80°C	est 50 – I _I O ((Test 7)) / i	2.08						7000		700∓	pA√℃
60 69 57 85 55 55 56 56 56 56 56 56 56 56 56 56 56	GND	-15 V		K5	2	E45	>	$+IIB = 10^{6} (E37 - E45) /RS$	-300	+0.1	-100	+0.1	PA
55 56 56 60 60 60 60 60 60 60 60 60 60 60 60 60	-28 V	13 V		3		E46	3	$+IIB = 10^{6} (E38 - E46) /RS$	-300	+0.1	-100	+0.1	3
57 58 58 60 60 60 61	GND	-1.4 V		3	3	E47	2	$+IIB = 10^{6} (E39 - E47) /RS$	-300	+0.1	-100	+0.1	3
59 60 60 61	-2.5 V	1.1 V		ä	3	E48	3	$+IIB = 10^{6} (E40 - E48) /RS$	-300	+0.1	-100	+0.1	ä
61 60 59	GND	-15 V		K6	3	E49	3	-IIB = 10 ⁶ (E49 –E37) /RS	-300	+0.1	-100	+0.1	пA
60 60 61	-28 V	13 V		3	3	E50	3	-IIB = 10 ⁶ (E50 –E38) /RS	-300	+0.1	-100	+0.1	3
09 19	GND	-1.4 V		3	3	E51	3	-IIB = 10 ⁶ (E51 –E39) /RS	-300	+0.1	-100	+0.1	3
19	-2.5 V	1.1 V		3	3	E52	3	-IIB = 10 ⁶ (E52 –E40) /RS	-300	+0.1	-100	+0.1	ä
	GND	-1.4 V		None	3	E53	3	+PSRR = (E53 – E54) x 40		±100		±100	μV/V
	GND	-1.4 V		None	,	E54	*			∓100		±100	=
4003 62 <u>4/</u> Calculate	Calculate value using data from tests 43 and 44.	data from test	s 43 and 4	4.				CMR = 20 log $ 2.8 \times 10^{4} / E37 - E38 $	92		92		dB
3011 63 <u>6</u> / 30 V	GND	GND -25 V		None	က	5	mA	lOS(+) = l5	-70		-70		μ
3005 64 <u>7</u> / 30 V	GND			None	7	9	МА	ICC = 16		4		4	ä
4004 65 30 V	GND	-30 V		Ж 8	က	(E0)1	>	+VOP = (E0)1	27		27		>
, 66 30 V	GND	-30 V		K7	8	(E ₀)2	ž	+VOP = (E0)2	26		26		×
" 67 30 V	GND	-26 V		K8	2	E55	3	AVS(+) = 25/(E56 - E55)	20		20		V/m/
30 V	GND	-1 \		К8	3	E56	3		50		20		3
" 68 30 V	GND	-20 V		K7	3	E57		AVS(+) = 15/(E58 - E57)	90		50		*
" 30 V	GND	-5 V		K7	n	E58	»		50		20		×

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

														Device	Device types	
Subgroup	Symbol	MIL-STD	Test		Adapte	Adapter pin numbers	bers	Ш	Energized					05,	05, 06	Unit
		-883	no.						relays <u>2</u> /	Ř	Measured pins	SU	Equations 3/	ij	Limits	
		method		1	2	က	4	2		No.	Value	Unit		Min	Мах	
4	AVS	4004	69	5 V	GND		-2.5 V		K8	2	E59	>	AVS(+) = 1.5/(E60 - E59)	10		V/m/V
TA =+25°C		3		5 V	GND		-1 V		К8	3	E60	3				3
		3	20	5 V	GND		-2.5 V		K7	3	E61	*	AVS(-) = 1.5/(E62 – E61)	10		:
''		ä		5 V	GND		-1 \		K7	"	E62	×				
	NOL	3007	71	30 V	GND		5 V		K11, K9	3	(E0)3	m/	VOL = (E0)3		35	V/m
		3	72	30 V	GND	5 mA	5 V		K11	3	(E0)4	>	VOL = (E0)4		1.5	>
'.		3	73	4.5 V	GND	2 µA	5 V		K11	3	(E0)5	:	VOL = (E0)5		0.4	3
	МОИ	3006	74	30 V	GND	-10 mA	-5 V		K11	3	(E ₀)6	*	VOH = (E0)6	27		3
	ΛОН	3006	75	4.5 V	GND	-10 mA	-5 V		K11	:	(E ₀)7	*	VOH = (E0)7	2.4		3
2	+VOP	4004	76	30 V	GND		-30 V		K8	3	(E0)8	*	+VOP = (E0)8	27		
TA =+125°C	-VOP	3	77	30 V	GND		-30 V		K7	"	(E0)9	*	-VOP = (E0)9	26		*
	AVS(+)	3	78	30 V	GND		-26 V		% 8	2	E63	:	AVS(+) = 25/(E64 – E63)	25		V/m/V
		ä		30 V	GND		-1 \		% %	3	E64	*				3
		ä	62	30 V	GND		-20 V		K7	3	E65	*	AVS(+) = 15/(E66 – E65)	25		3
'.		3		30 V	GND		-5V		K7	3	E66	3				3
	Avs	3	80	2 \	GND		-2.5 V		8 8	3	E67	2	AVS = 1.5/(E68 – E67)	10		//m//
		3		5 V	GND		> 1-		88	3	E68					3
		z	81	5 V	GND		-2.5 V		K7	*	E69	3	AVS = 1.5/(E70 – E69)	10		3
'.		3		5 V	GND		> 1-		ΚŻ	ä	E70	3				3
	VOL	3007	82	30 V	GND		5 \		K11, K9	က	(E0)10	NW.	VOL = (E0)10		35	/m
		3	83	30 V	GND	5 mA	5 V		K11	3	(E0)11	>	VOL = (E0)11		1.5	>
•		z	84	4.5 V	GND	2 µA	5 V		K11	3	(E0)12	3	VOL = (E0)12		0.4	3
	VОН	3006	85	30 V	GND	-10 mA	-5 V		K11	3	(E ₀)13	*	VOH = (E0)13	27		3
	МОН	3006	86	4.5 V	GND	-10 mA	-5 V		K11	3	(E0)14	"	VOH = (E0)14	2.4		*

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

													Device types	types	
Symbol	MIL-STD	Test		Adapt	Adapter pin numbers	bers		Energized					02, 06	90	Unit
	-883	0						relays 2/	M	Measured pins	ins	Equations 3/	Limits	iits	
	method		1	2	3	4	5		No.	Value	Unit		Min	Мах	
+VOP	4004	87	30 V	GND		-30 V		K8	3	(E0)15	>	+VOP = (E0)15	27		>
+VOP	3	88	30 V	GND		-30 V		K7	"	(E0)16	3	+VOP = (E0)16	26		>
AVS(+)	3	68	30 V	GND		-26 V		K8	5	E71	3	AVS(+) = 25/(E72 - E71)	25		V/mV
	3		30 V	GND		-1 V		K8	3	E72	3		25		3
	3	06	30 V	GND		-20 V		K7	3	E73	3	AVS(+) = 15/(E74 - E73)	25		3
	3		30 V	GND		-5 V		K7	3	E74	3		25		3
AVS	3	91	5 V	GND		-2.5 V		K8	ä	E75	3	AVS = 1.5/(E76 – E75)	10		3
	3		5 V	GND		-1 V		K8	n	E76	3				3
	3	92	5 V	GND		-2.5 V		К7	3	E77	3	AVS = 1.5/(E78 – E77)	10		3
	"		5 V	GND		-1 V		K7	"	E78	×				"
NOL	3007	93	30 V	GND		5 V		K11, K9	3	(E0)17	νm	VOL = (E0)17		35	νm
	3	94	30 V	GND	5 mA	5 V		K11	3	(E0)18	>	VOL = (E0)18		1.5	>
	3	92	4.5 V	GND	2 µA	5 V		K11	3	(E0)19	3	VOL = (E0)19		0.4	3
МОМ	3006	96	30 V	GND	-10 mA	-5 V		K11	:	(E0)20	:	VOH = (E0)20	27		=
МОМ	3006	26	4.5 V	GND	-10 mA	-5 V		K11	3	(E0)21	3	VOH = (E0)21	2.3		ä
NI(BB)		98 <u>10</u> /	15 V	-15 V		GND		K10, K11	3	(E0)22	mVrms	NI(BB) = (E ₀)22		15	μVrms
NI(PC)		99 10/	15 V	-15 V		GND		K5,K6,K10, K11	n	(E0)23	mVpk	NI(PC) = (E0)23		50	μVpk
SS		100	30 V	GND	16 V	-1.4 V		See fig. 3	2	E79	>	$CS = 20 \log$	80		명
			30 V	GND	> 1	-1.4 V		3	3	E80	3	1.5 x 10 / E79 – E80	80		3
		101	30 V	GND	16 V	-1.4 V		:	:	E81	:	$CS = 20 \log_4$	80		=
			30 V	GND	1 \	-1.4 V		3	3	E82	3	1.5 x 10	80		3
		102	30 V	GND	16 V	-1.4 V		3	3	E83	3	$CS = 20 \log$	80		3
			30 V	GND	1 \	-1.4 V		3	:	E84	3	1.5 x 10	80		3
		103	30 V	GND	16 V	-1.4 V		=	:	E85	3	$CS = 20 \log$	80		:
			30 V	GND	1 \	-1.4 V		3	3	E86	3	1.5 × 10	80		3

TABLE III. Group A inspection for device types 05 and 06 - Continued. 1/

														Device types	types	
Symbol MIL-STD Test Adapter pin numbers	MIL-STD Test		Adapter pin numbers	Adapter pin numbers	ır pin numbers	nbers			Energized					05, 05	05	Unit
-883 no.		no.	-	-	-				relays <u>2</u> /		Measured pins	S	Equations $3/$	Limits	its	
method 1 2 3 4	1 2 3	ъ	ъ	ъ		4		5		No.	Value	Unit		Min	Max	
CS 104 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4 V			See fig. 3	2	E87	>	$CS = 20 \log_{4}$	80		ВВ
30 V GND 1 V -1.4 V	GND 1 V	GND 1 V	GND 1 V	1 \		-1.4 V			z		E88	3	1.5 x 10	80		3
105 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4 V			3		E89	3	$CS = 20 \log_{4}$	80		3
30 V GND 1 V -1.4 V	GND 1 V	GND 1 V	GND 1 V	1 \		-1.4 V	_		*		E90	3	1.5 × 10	80		*
106 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4 V	-		3		E91	3	$CS = 20 \log 4$	80		*
30 V GND 1 V -1.4 V	GND 1 V	GND 1 V	GND 1 V	1 \		-1.4 V			z		E92	3	1.5 x 10	80		3
107 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4	_		3		E93	3	$CS = 20 \log_{4}$	80		3
30 V GND 1 V -1.4 V	GND 1 V	GND 1 V	GND 1 V	1 \		-1.4	_		3		E94	3	1.5 x 10	80		3
108 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4 V			2		E95	ä	$CS = 20 \log_{14}$	80		*
30 V GND 1 V -1.4 V	GND 1 V	GND 1 V	GND 1 V	> +		-1.4	>		*		96 <u>3</u>	3	1.5 × 10 / E95 – E96	80		3
109 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4	>		2		E97	3	CS = 20 log	80		3
30 V GND 1V -1.4 V	GND 1 V	GND 1 V	GND 1 V	7 \		-1.4	>		*		E98	ä	1.5 × 10 × 15 1.5	80		ä
110 30 V GND 16 V -1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4	`		2		E99	3	$CS = 20 \log_{14.5 \times 14.5}$	80		3
30 V GND 1V -1.4 V	GND 1 V	GND 1 V	GND 1 V	1 \		-1.4	>		3		E100	z		80		3
111 30 V GND 16 V-1.4 V	30 V GND 16 V	30 V GND 16 V	GND 16 V	16 V		-1.4	`		ä	'	E101	3	$CS = 20 \log_{14.5 \times 10^{-1}}$	80		3
30 V GND 1V -1.4 V	GND 1 V	GND 1 V	GND 1 V	7 \		-1.4	>		#	'	E102	ä		80		ä
TR(t _r) 112 30 V GND IN	30 V GND	30 V GND	GND		Z			ОПТ	See fig. 4	'	Δt	sπ	(Waveform 1) TR(t_f) = Δt		1.0	sn
TR(os) 113 30 V GND IN	30 V GND	30 V GND	GND		Z			OUT	3	•	VO;ΔVO	>	(Waveform 1) TR(OS) = 100 (∆VO/VO)		09	%
SR(+) 4002 114 30 V GND IN	114 30 V GND	30 V GND	GND		Z			OUT	3		ΔVO; Δt	V; µs	(Waveform 2) $SR(+) = VO/\Delta t$	0.1		V/µs
SR(-) " 115 30 V GND IN	115 30 V GND	30 V GND	GND		Z			ОПТ	я		ΔVO; Δt	V; µs	(Waveform 3) SR(-) = $\Delta VO/\Delta t$	0.1		V/µs
116 to Same tests, terminal conditions and limits as subgroup 7, tests 112 through 115 except TA = 125°C and TA = -55°C.			Same tests, terminal conditions ar	sts, terminal conditions ar	al conditions ar	ions ar	iii	mits as sı	ubgroup 7, te	ests 112	through 115 e	xcept TA =	= 125° C and TA = -55° C.			

TABLE III. Group A inspection - Continued.

1/ Use table III in conjunction with the following:

<u>Tests</u>	Device type	<u>Figure</u>
1 – 102	01 - 04	2
1 – 99	05 - 06	
103 – 114	01 - 04	3
100 – 111	05 - 06	
115 – 126	01 - 04	4
112 - 123	05 - 06	

- 2/ K1, K2, K3, or K4 relay will also be energized as follows:
 - a. Device types 01 through 04 test numbers 22 and 103 through 126.
 - b. Device types 05 and 06 test numbers 20 and 100 through 123.
- 3/ The equations take into account both the closed loop gain of 1,000 and the scale factor multiplier so that the calculator value is in table I units; therefore, use the measured value units in the equation.
 (For example: If E₁ = 2 V and V_{IO} = E₁, then V_{IO} = E₁, then V_{IO} = 2 mV).
- 4/ Each device shall be tested over the common mode range as specified in table III with the output forced to the worse case condition. V_{CM} is achieved by grounding the inputs and algebraically subtracting V_{CM} from each supply. Common mode rejection is calculated using the offset voltage values measured at the common mode range end points.
- 5/ In device types 01 through 04, to minimize thermal drift, the reference voltage for gain measurement (E₃, E₂₁, and E₃₉) shall be taken immediately prior to or after the reading corresponding to device gain (E₅₅, E₅₆, E₅₇, E₅₈, E₆₃, E₆₄, E₆₅, E₆₆, E₇₁, E₇₂, E₇₃, and E₇₄).
- 6/ Only one amplifier shall be tested at one time and its output shall be shorted to ground for 25 ms or less.
- 7/ Each amplifier shall be tested separately, except for the I_{CC} measurements where all the amplifiers shall be connected as grounded followers (relays K1 through K4 de-energized).
- 8/ Tests 27, 32, 51, and 56 for devices types 01 through 04 and tests 25, 30, 47, and 52 for device types 05 and 06, which require a read and record measurement plus a calculation, may be omitted except when subgroups 2 and 3 are being accomplished for group A sampling inspection and groups C and D end point measurement.
- 9/ SR(+) and SR(-) are 0.2 V/µs for device type 01 and 0.8 V/µs for device type 02.
- 10/ Broadband noise (NI(BB) shall be measured using an rms voltmeter with a bandwidth of 10 Hz to 5 kHz. "Popcorn" noise (NI(PC)) shall be measured for 15 seconds.
- 11/ For device types 01, 03, and 04, $V_{IN} = 10 \text{ V}$; for device type 02, $V_{IN} = 2 \text{ V}$.
- $\underline{12}$ / For device types 01, 03, and 04, $V_{IN} = -10 \text{ V}$; for device type 02, $V_{IN} = -2 \text{ V}$.

TABLE IV. Group C and Group B life test end point electrical parameters.

(T_A = +25°C, \pm V_{CC} = \pm 20 V for device types 01 – 04 and +V_{CC} = 30 V for device types 05 and 06).

Table III test no.	Test		01,	02			0	3		Unit
		Lir	mit	De	elta	Lir	mit	De	elta	
		Min	Max	Min	Max	Min	Max	Min	Max	
3	V _{IO}	-5	+5	-1	+1	-3.0	+3.0	-0.5	+0.5	mV
11	+l _{IB}	+0.1	+100	-15	+15	-200	-1	-20	20	nA
15	-I _{IB}	+0.1	+100	-15	+15	-200	-1	-20	20	nA

Table III test no.	Test		0	4			0	5		Unit
		Lir	nit	De	elta	Lir	nit	De	elta	
		Min	Max	Min	Max	Min	Max	Min	Max	
3	V _{IO}	-5	+5	-1	+1	-5	+5	-1	+1	mV
11	+l _{IB}	-250	-1	-25	+25	-150	-1	-15	+15	nA
15	-I _{IB}	-250	-1	-25	+25	-150	-1	-15	+15	nA

Table III test no.	Test		0	6		Unit
		Lir	mit	De	elta	
		Min	Max	Min	Max	
3	V _{IO}	-2	+2	-0.5	+0.5	mV
11	+l _{IB}	-50	-1	-10	+10	nA
15	-I _{IB}	-50	-1	-10	+10	nA

 $\underline{1}$ / For device types 05 and 06, the table III test numbers are as follows: V_{IO} use test number 1, + I_{IB} use the test number 9, - I_{IB} use test number 13.

- 4.4 <u>Technology Conformance inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 9, 10, and 11 shall be omitted.
 - 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.
 - 4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:
 - a. End point electrical parameters shall be as specified in table II herein.
 - b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- 4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End point electrical parameters shall be as specified in table II herein.
 - 4.5 Methods of inspection. Methods of inspection shall be specified and as follows.
- 4.5.1 <u>Voltage and current</u>. All voltage values given are referenced to the external zero reference level of the supply voltage. Currents given are for conventional current and are positive when flowing into the referenced terminal.
- 4.5.2 <u>Life test cooldown procedure</u>. When devices are measured at +25°C following application of the steady state life or burn-in test condition, they shall be cooled to within 10°C of their power stable condition at room temperature prior to removal of the bias.

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this specification are intended for Government microcircuit applications (original equipment) and logistic purposes.

- 6.2 Ordering data. The contract or purchase order should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to acquiring activity in addition to notification of the qualifying activity, if applicable.
 - Requirements for failure analysis (including required test condition of MIL-STD-883, method 5003), corrective action and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - Requirements for "JAN" marking.
 - j. Packaging requirements (see 5.1).
- 6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.
- 6.4 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43213-1199.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-STD-1331.
- 6.6 <u>Logistic support</u>. Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired to Government logistic support will be acquired to device class B (see 1.2.2), and lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.
- 6.7 <u>Substitutability</u>. The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-M-38535.

Military device type	Generic-industry type
01	LM148
02	LM149
03	4741, 4156
04	4136
05	LM124
06	LM124A

6.7 Changes from previous issue. Asterisks are not used in this revision to identify changes with respect to the previous issue, due to the extensiveness of the changes.

Custodians:

Army - CR Navý - EC Air Force - 11

NASA - NA

DLA - CC

Review activities:

Army - MI, SM

Navy - AS, CG, MC, SH, TD

Air Force – 03, 19, 99

Preparing activity: DLA - CC

Project 5962-1976

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

- 1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
- 2. The submitter of this form must complete blocks 4, 5, 6, and 7, and send to preparing activity.
- 3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts.

Comments submitted on this form do not co contractual requirements.	onstitute or imply authorization to waive an	ny portion of the referenced document(s) or to amend
I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-M-38510/110C	2. DOCUMENT DATE (YYYYMMDD) 2003/08/19
3. DOCUMENT TITLE	•	
MICROCIRCUITS, LINEAR, QUAD OPERAT M38510/10106	IONAL AMPLIFIERS, MONOLITHIC SILIC	CON, PART NUMBERS M38510/10101 THROUGH
4. NATURE OF CHANGE (Identify paragrap	h number and include proposed rewrite, it	f possible. Attach extra sheets as needed.)
5. REASON FOR RECOMMENDATION		
o. Remoditi on Redommend/mon		
6. SUBMITTER a. NAME (Last, First Middle Initial)	b. ORGANIZATI	ON
a. NAIVIE (Last, Filst Middle Illidai)	b. ORGANIZATI	ON
c. ADDRESS (Include Zip Code)	d. TELEPHONF	(Include Area Code) 7. DATE SUBMITTED
o. 7.221.233 (molado 2.p. 3343)	(1) Commercial	(YYYYMMDD)
	(2) DSN	
	(If applicable)	
3. PREPARING ACTIVITY		
a. NAME	b. TELEPHONE	(Include Area Code
Rick Officer	(1) Commercial	(2) DSN
	614-692-051	
c. ADDRESS (Include Zip Code)		RECEIVE A REPLY WITHIN 45 DAYS, CONTACT:
DSCC-VAS		dardization Program Office (DLSC-LM)
3990 East Broad Street		Kingman Road, Suite 2533
Columbus, Ohio 43216-5000		irginia 22060-6221
DD Form 1426 FEB 1999 (FG)		3)767-6888 DSN 427-6888

DD Form 1426, FEB 1999 (EG) WHS/DIOR, Feb 99